

Silicon NPN Power Transistors

2SC1469

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For high voltage ,fast switching applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

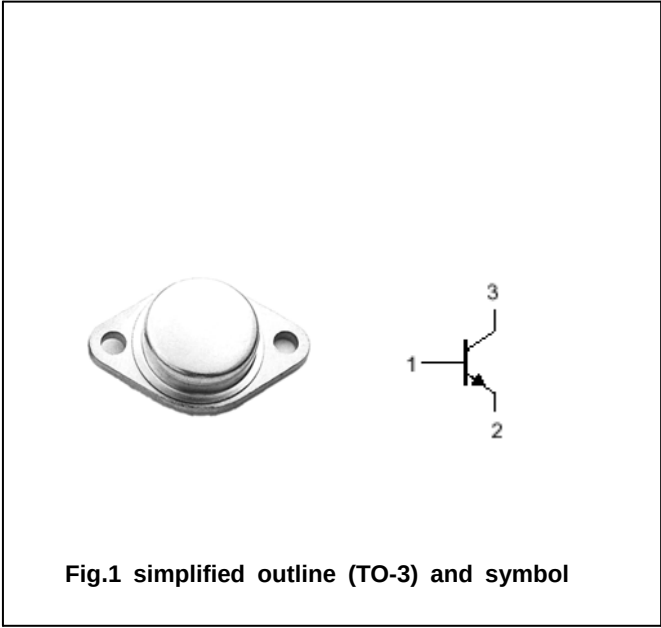


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		10	A
I _B	Base current		4	A
P _T	Total power dissipation	T _C ≤25℃	100	W
T _j	Junction temperature		200	℃
T _{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.25	℃/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =1A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			0.1	mA
I _{CEO}	Collector cut-off current	V _{CE} =400V; I _B =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	15		50	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	8			
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		10		MHz

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PACKAGE OUTLINE

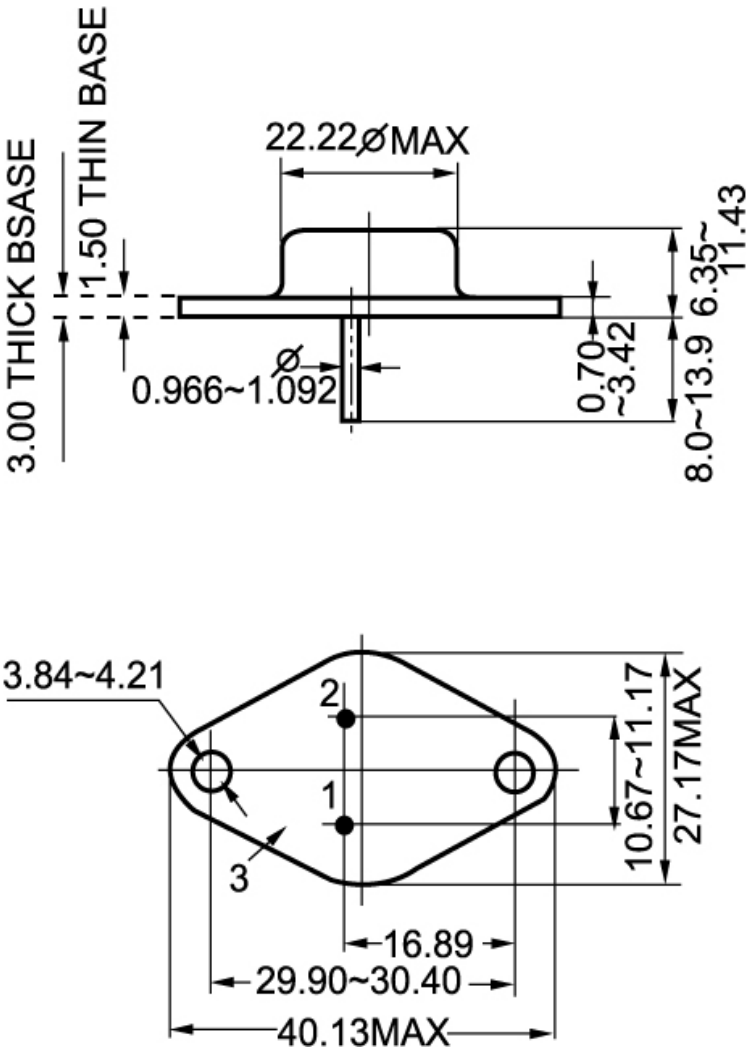


Fig.2 Outline dimensions